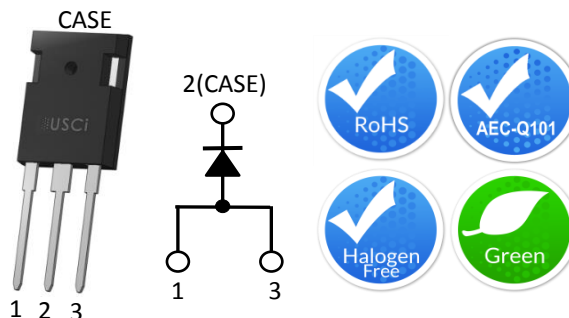


Description

United Silicon Carbide, Inc. offers the 3rd generation of high performance SiC Merged-PiN-Schottky (MPS) diodes. With zero reverse recovery charge and 175°C maximum junction temperature, these diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.



Part Number	Package	Marking
UJ3D1250K	TO-247-3L	UJ3D1250K

Features

- ♦ 175°C maximum operating junction temperature
- ♦ Easy paralleling
- ♦ Extremely fast switching not dependent on temperature
- ♦ No reverse or forward recovery
- ♦ Enhanced surge current capability, MPS structure
- ♦ 100% UIS tested
- ♦ AEC-Q101 qualified

Typical Applications

- ♦ Power converters
- ♦ Industrial motor drives
- ♦ Switching-mode power supplies
- ♦ Power factor correction modules

Maximum Ratings

Parameter	Symbol	Test Conditions	Value	Units
DC blocking voltage	V_R		1200	V
Repetitive peak reverse voltage, $T_J=25^\circ\text{C}$	V_{RRM}		1200	V
Surge peak reverse voltage	V_{RSM}		1200	V
Maximum DC forward current	I_F	$T_C = 112^\circ\text{C}$	50	A
Non-repetitive forward surge current sine halfwave	I_{FSM}	$T_C = 25^\circ\text{C}$, $t_p = 10\text{ms}$	275	A
Repetitive forward surge current sine halfwave, $D=0.1$	I_{FRM}	$T_C = 25^\circ\text{C}$, $t_p = 10\text{ms}$	163.5	A
		$T_C = 110^\circ\text{C}$, $t_p = 10\text{ms}$	99.6	
Non-repetitive peak forward current	$I_{F,max}$	$T_C = 25^\circ\text{C}$, $t_p = 10\mu\text{s}$	2400	A
		$T_C = 110^\circ\text{C}$, $t_p = 10\mu\text{s}$	2400	
i^2t value	$\int i^2 dt$	$T_C = 25^\circ\text{C}$, $t_p = 10\text{ms}$	378	A^2s
Power dissipation	P_{Tot}	$T_C = 25^\circ\text{C}$	319	W
		$T_C = 112^\circ\text{C}$	134	
Maximum junction temperature	$T_{J,max}$		175	$^\circ\text{C}$
Operating and storage temperature	T_J , T_{STG}		-55 to 175	$^\circ\text{C}$
Soldering temperatures, wavesoldering only allowed at leads	T_{sold}	1.6mm from case for 10s	260	$^\circ\text{C}$

Electrical Characteristics

$T_J = +25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Forward voltage	V_F	$I_F = 50\text{A}, T_J = 25^\circ\text{C}$	-	1.5	1.7	V
		$I_F = 50\text{A}, T_J = 150^\circ\text{C}$	-	1.95	2.4	
		$I_F = 50\text{A}, T_J = 175^\circ\text{C}$	-	2.2	2.7	
Reverse current	I_R	$V_R = 1200\text{V}, T_J = 25^\circ\text{C}$	-	500	1250	μA
		$V_R = 1200\text{V}, T_J = 175^\circ\text{C}$	-	3500		
Total capacitive charge ⁽¹⁾	Q_C	$V_R = 800\text{V}$		240		nC
Total capacitance	C	$V_R = 1\text{V}, f = 1\text{MHz}$		2340		pF
		$V_R = 400\text{V}, f = 1\text{MHz}$		224		
		$V_R = 800\text{V}, f = 1\text{MHz}$		198		
Capacitance stored energy	E_C	$V_R = 800\text{V}$		72		μJ

(1) Q_C is independent on T_J , di_F/dt , and I_F as shown in the application note USCi_AN0011.

Thermal characteristics

Parameter	symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Thermal resistance, junction - case	$R_{\theta JC}$			0.36	0.47	$^\circ\text{C/W}$

Typical Performance

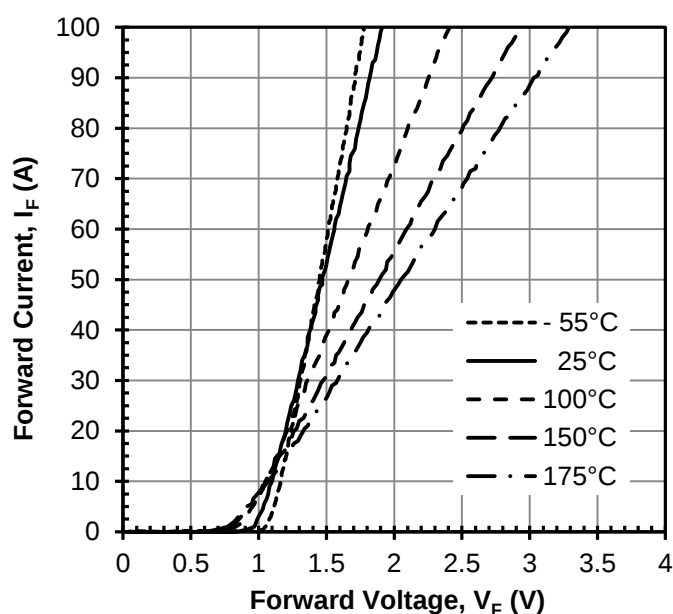


Figure 1 Typical forward characteristics

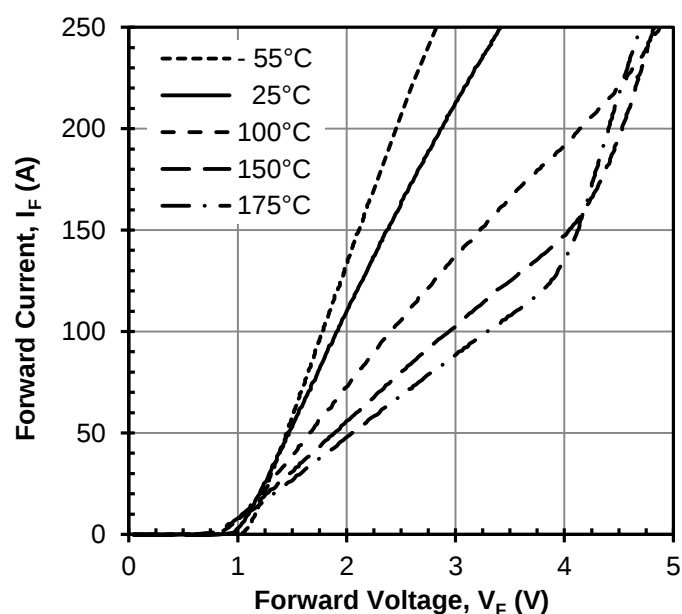


Figure 2 Typical forward characteristics in surge current

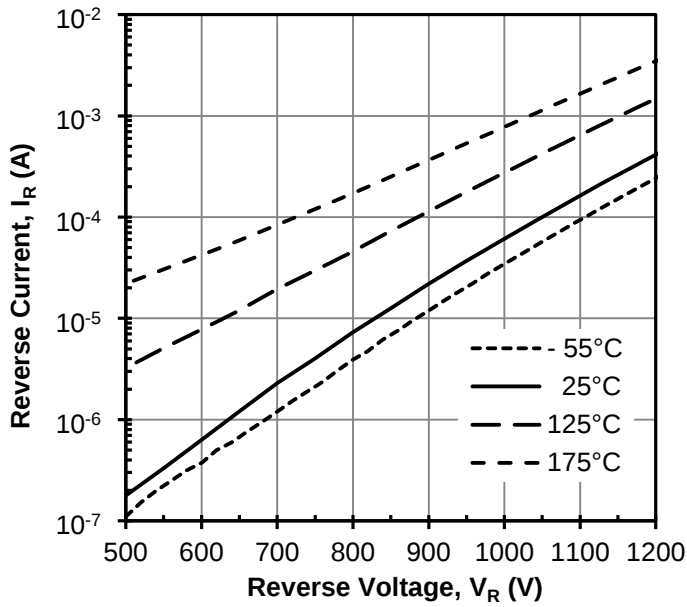


Figure 3 Typical reverse characteristics

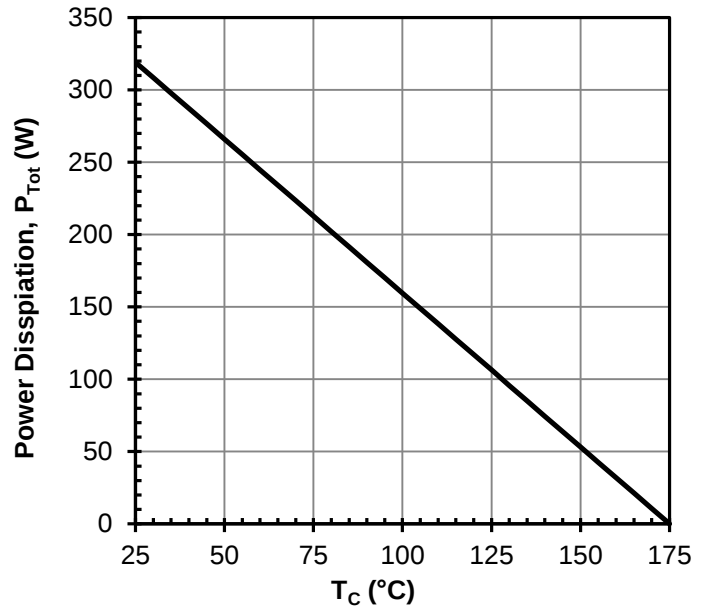


Figure 4 Power dissipation

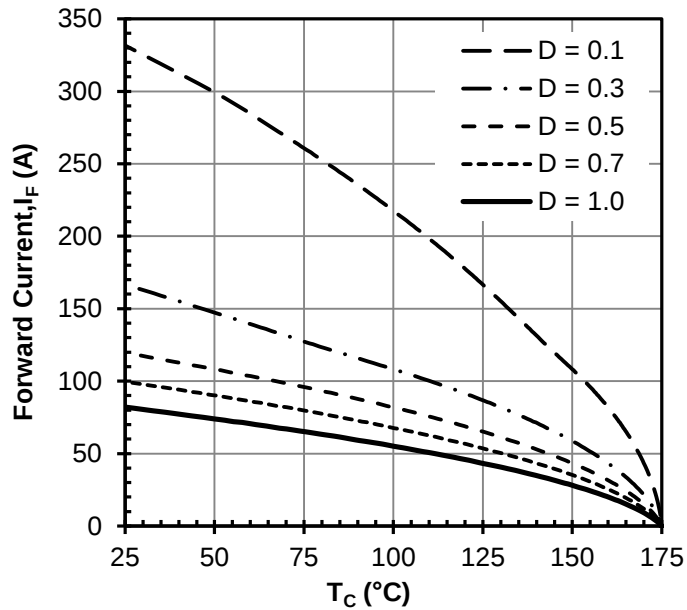


Figure 5 Diode forward current

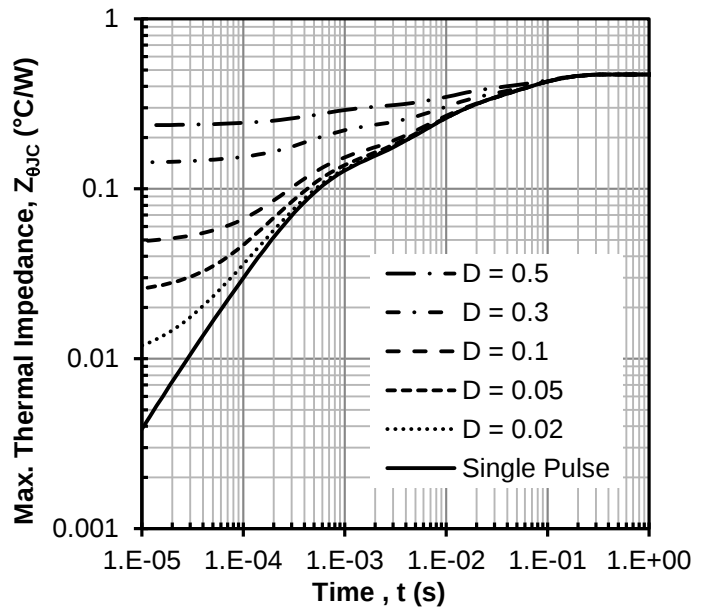


Figure 6 Maximum transient thermal impedance

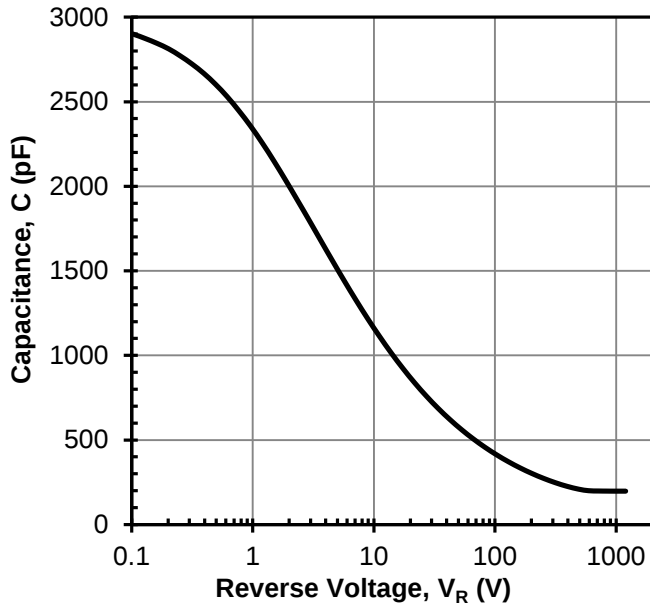


Figure 7 Capacitance vs. reverse voltage at 1MHz

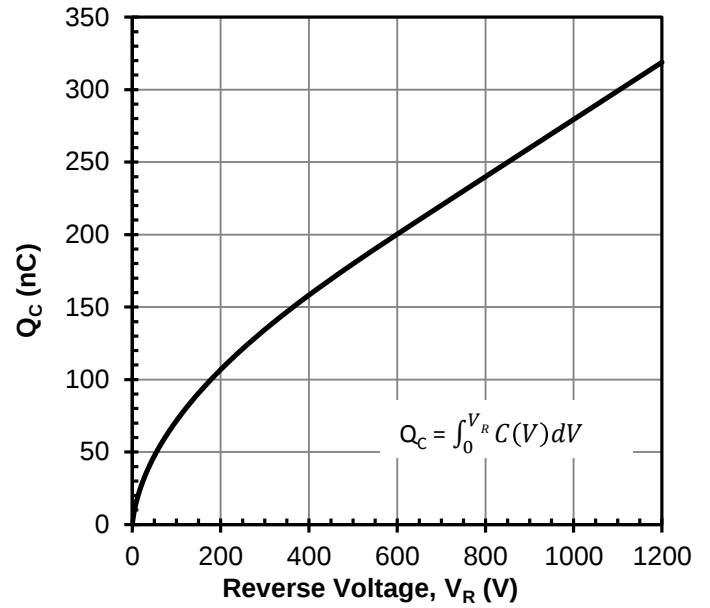


Figure 8 Typical capacitive charge vs. reverse voltage

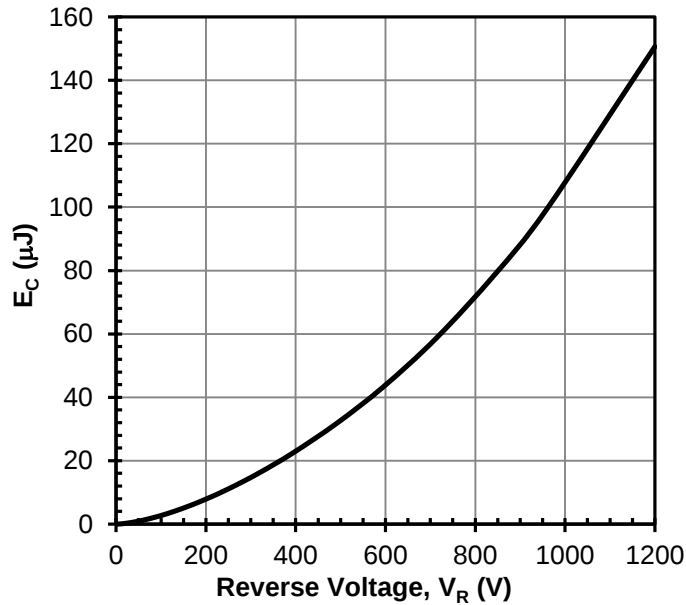


Figure 9 Typical capacitance stored energy vs. reverse voltage

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